

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE (L<sup>2</sup>-π-MOSV)

# 2SK2201

HIGH SPEED, HIGH CURRENT SWITCHING APPLICATIONS  
 CHOPPER REGULATOR, DC-DC CONVERTER AND MOTOR DRIVE APPLICATIONS

INDUSTRIAL APPLICATIONS  
 Unit in mm

- 4V Gate Drive
- Low Drain-Source ON Resistance :  $R_{DS(ON)} = 0.28\Omega$  (Typ.)
- High Forward Transfer Admittance :  $|Y_{fs}| = 3.5S$  (Typ.)
- Low Leakage Current :  $I_{DSS} = 100\mu A$  (Max.) ( $V_{DS} = 100V$ )
- Enhancement-Mode :  $V_{th} = 0.8 \sim 2.0V$  ( $V_{DS} = 10V, I_D = 1mA$ )

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	$V_{DSS}$	100	V
Drain-Gate Voltage ( $R_{GS} = 20k\Omega$ )	$V_{DGR}$	100	V
Gate-Source Voltage	$V_{GSS}$	$\pm 20$	V
Drain Current	DC	$I_D$	3 A
	Pulse	$I_{DP}$	12 A
Drain Power Dissipation ( $T_c = 25^\circ C$ )	$P_D$	20	W
Single Pulse Avalanche Energy**	$E_{AS}$	140	mJ
Avalanche Current	$I_{AR}$	3	A
Repetitive Avalanche Energy*	$E_{AR}$	2	mJ
Channel Temperature	$T_{ch}$	150	°C
Storage Temperature Range	$T_{stg}$	-55~150	°C

THERMAL CHARACTERISTICS

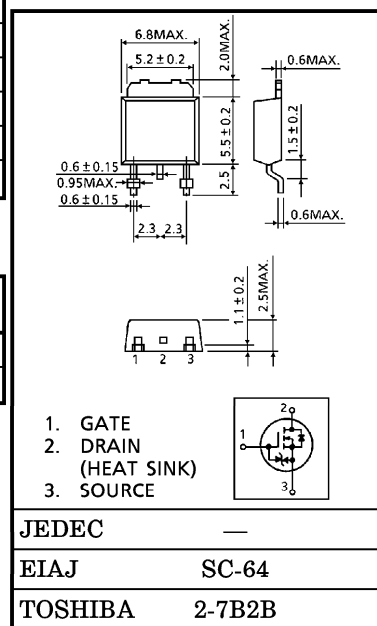
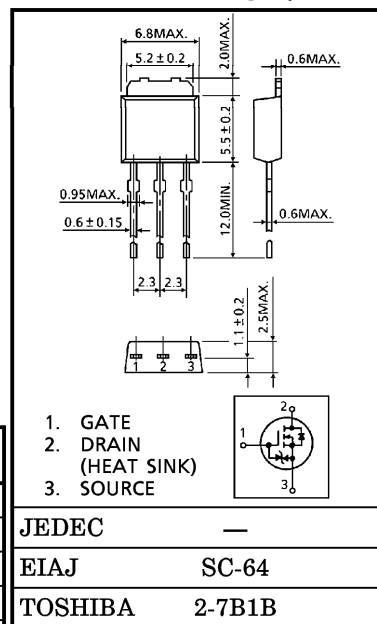
CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel To Case	$R_{th(ch-c)}$	6.25	°C/W
Thermal Resistance, Channel To Ambient	$R_{th(ch-a)}$	125	°C/W

Note ;

\* Repetitive rating ; Pulse Width Limited by Max. junction temperature.

\*\*  $V_{DD} = 50V$ , Starting  $T_{ch} = 25^\circ C$ ,  $L = 25mH$ ,  $R_G = 25\Omega$ ,  $I_{AR} = 3A$

**This transistor is an electrostatic sensitive device. Please handle with caution.**



Weight : 0.36g

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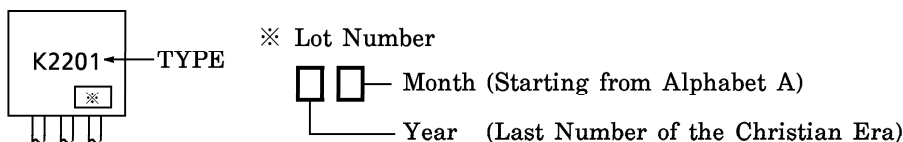
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

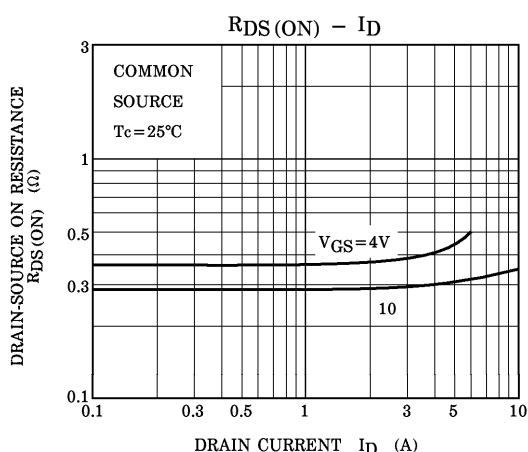
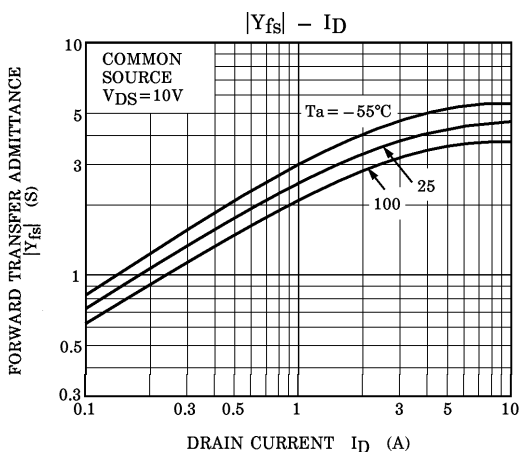
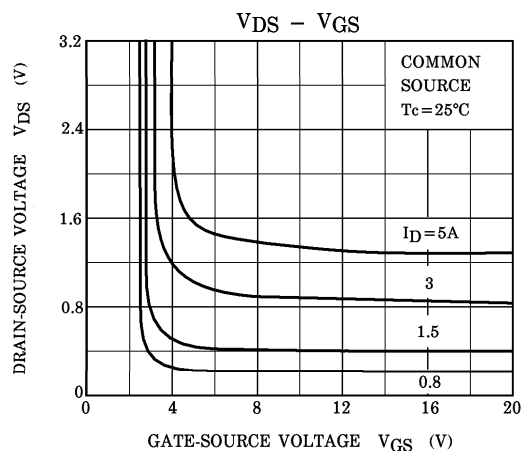
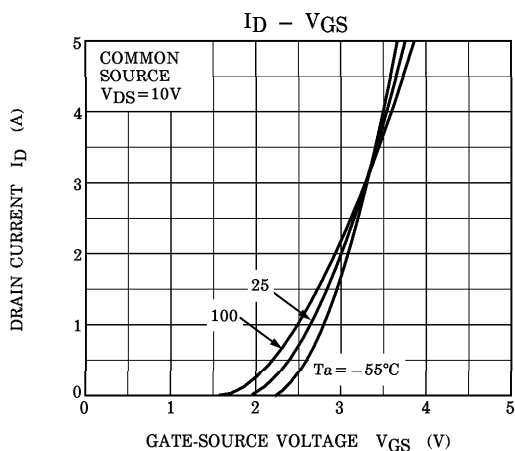
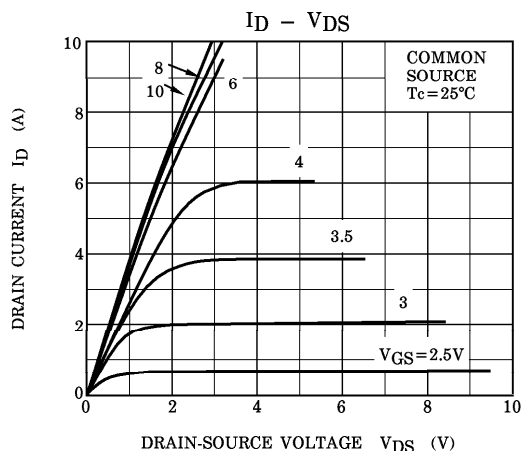
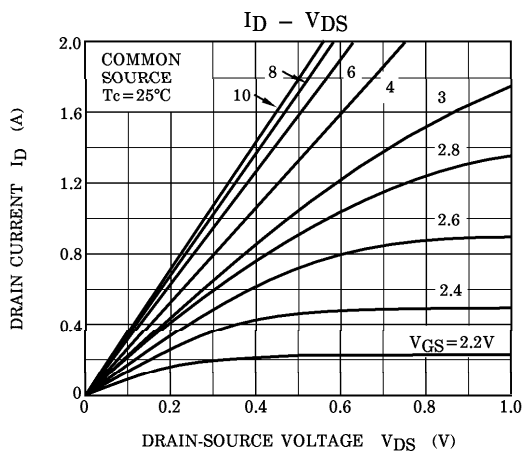
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		$I_{GSS}$	$V_{GS} = \pm 16V, V_{DS} = 0V$	—	—	$\pm 10$	$\mu A$
Drain Cut-off Current		$I_{DSS}$	$V_{DS} = 100V, V_{GS} = 0V$	—	—	100	$\mu A$
Drain-Source Breakdown Voltage		$V(BR)_{DSS}$	$I_D = 10mA, V_{GS} = 0V$	100	—	—	V
Gate Threshold Voltage		$V_{th}$	$V_{DS} = 10V, I_D = 1mA$	0.8	—	2.0	V
Drain-Source ON Resistance		$R_{DS(ON)}$	$V_{GS} = 4V, I_D = 2A$	—	0.36	0.45	$\Omega$
			$V_{GS} = 10V, I_D = 2A$	—	0.28	0.35	
Forward Transfer Admittance		$ Y_{fs} $	$V_{DS} = 10V, I_D = 2A$	1.5	3.5	—	S
Input Capacitance		$C_{iss}$	$V_{DS} = 10V, V_{GS} = 0V$ $f = 1MHz$	—	280	—	pF
Reverse Transfer Capacitance		$C_{rss}$		—	50	—	
Output Capacitance		$C_{oss}$		—	105	—	
Switching Time	Rise Time	$t_r$	<p><math>I_D = 2A</math> <math>V_{GS} = 10V</math> <math>V_{DD} = 50V</math> <math>R_L = 25\Omega</math> <math>50\Omega</math></p> <p><math>V_{IN} : t_r, t_f &lt; 5ns,</math> <math>Duty \leq 1\%, t_w = 10\mu s</math></p>	—	20	—	ns
	Turn-on Time	$t_{on}$		—	50	—	
	Fall Time	$t_f$		—	40	—	
	Turn-off Time	$t_{off}$		—	170	—	
Total Gate Charge (Gate-Source Plus Gate-Drain)		$Q_g$	$V_{DD} = 80V, V_{GS} = 10V$ $I_D = 3A$	—	13.5	—	nC
Gate-Source Charge		$Q_{gs}$		—	8.5	—	
Gate-Drain ("Miller") Charge		$Q_{gd}$		—	5	—	

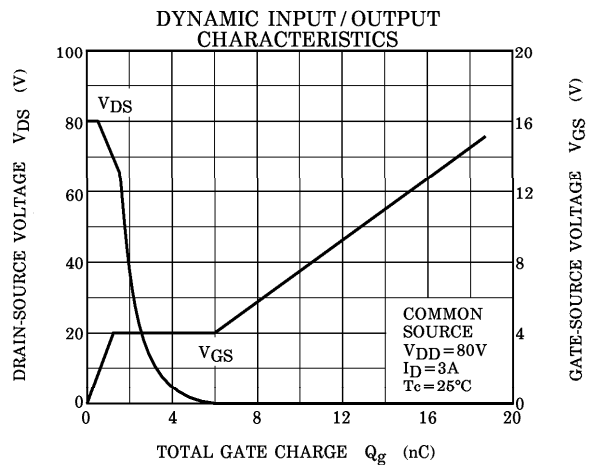
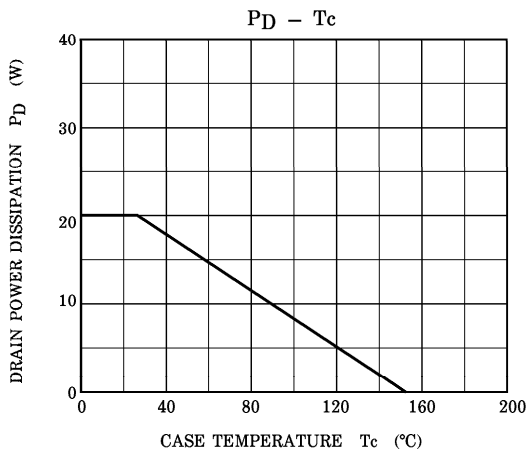
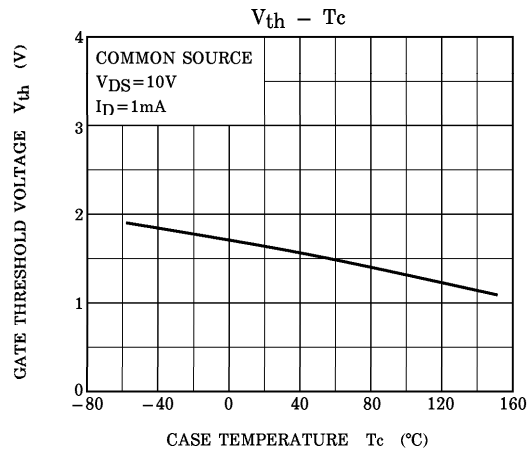
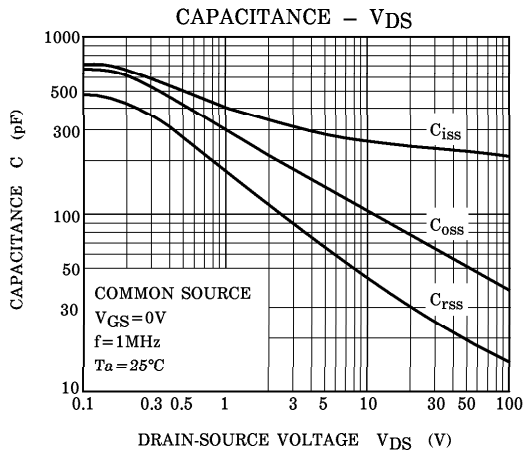
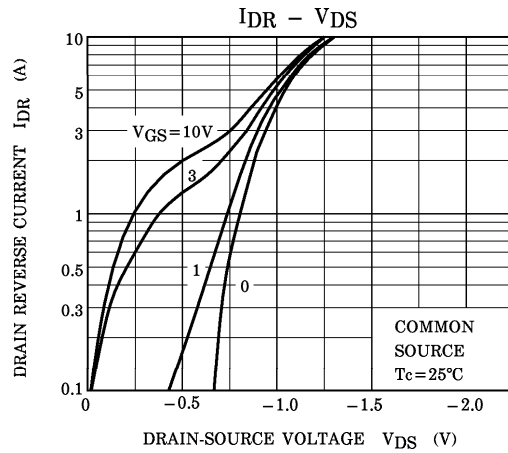
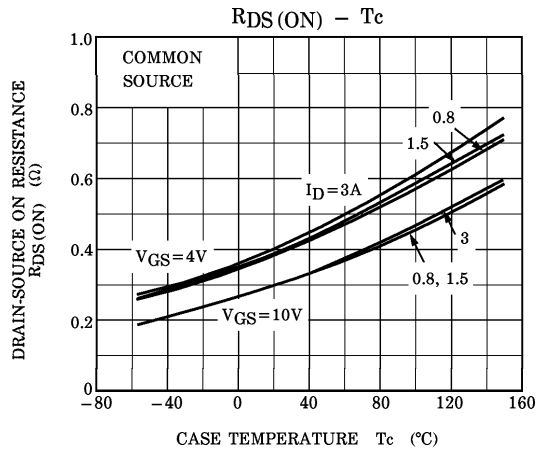
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

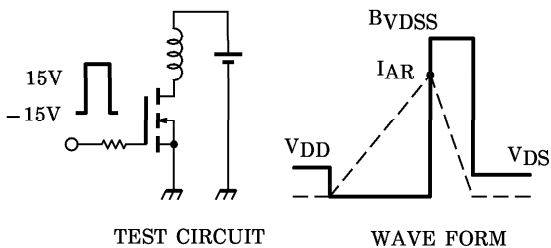
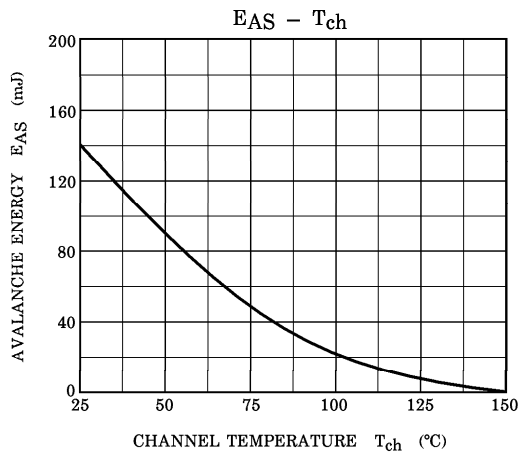
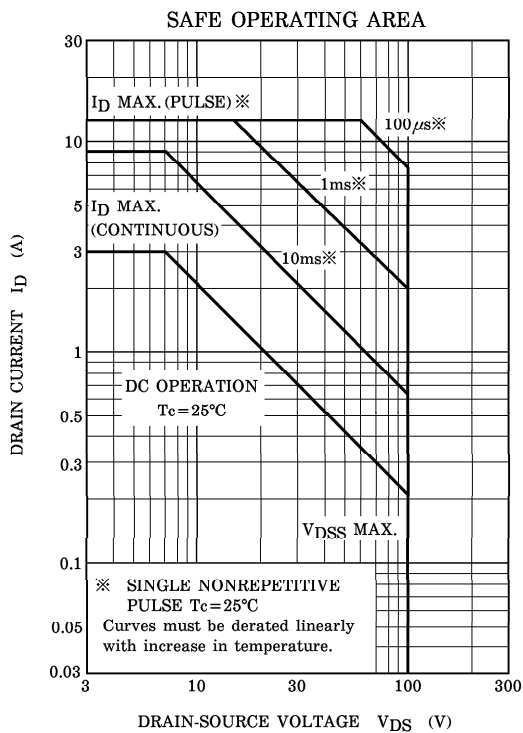
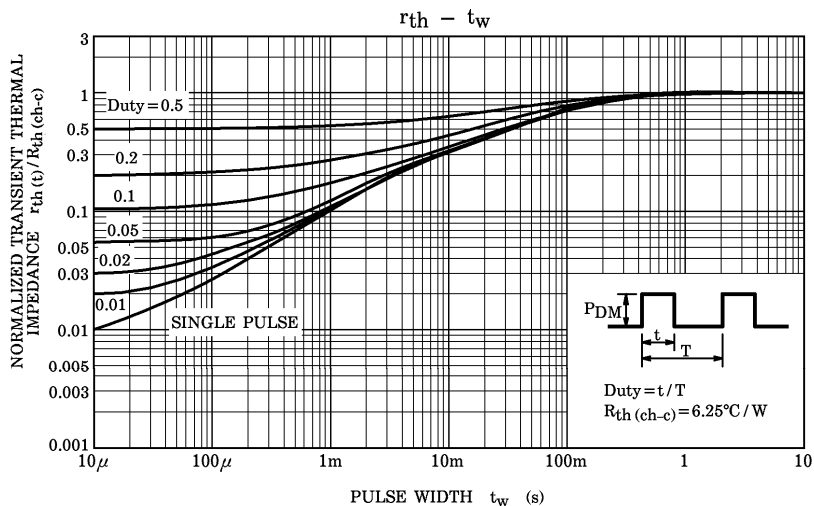
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	$I_{DR}$	—	—	—	3	A
Pulse Drain Reverse Current	$I_{DRP}$	—	—	—	12	A
Diode Forward Voltage	$V_{DSF}$	$I_{DR} = 3A, V_{GS} = 0V$	—	—	-1.5	V
Reverse Recovery Time	$t_{rr}$	$I_{DR} = 3A, V_{GS} = 0V$	—	100	—	ns
Reverse Recovery Charge	$Q_{rr}$	$dI_{DR} / dt = 50A / \mu s$	—	0.2	—	$\mu C$

MARKING









Peak  $I_{AR} = 3A$ ,  $R_G = 25\Omega$   
 $V_{DD} = 25V$ ,  $L = 25mH$

$$EAS = \frac{1}{2} \cdot L \cdot I^2 \cdot \left( \frac{BVDSS}{BVDSS - V_{DD}} \right)$$